# NXP BLP10H605 transistor datasheet

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A 5 W plastic LDMOS power transistor for broadcast transmitter and ISM applications at frequencies from HF to 1400 MHz.

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# **BLP10H605**

# **Broadband LDMOS driver transistor**

Rev. 1 — 21 February 2014

**Objective data sheet** 

# 1. Product profile

#### 1.1 General description

A 5 W plastic LDMOS power transistor for broadcast transmitter and ISM applications at frequencies from HF to 1400 MHz.

Table 1. Application performance

Test signal	f	V <sub>DS</sub>	P <sub>L</sub>	G <sub>p</sub>	$\eta_D$
	(MHz)	(V)	(W)	(dB)	(%)
CW	860	50	5	22.4	59.6

#### 1.2 Features and benefits

- Easy power control
- Integrated dual side ESD protection
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (HF to 1400 MHz)
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

### 1.3 Applications

- Industrial, scientific and medical applications
- Broadcast transmitter applications



# 2. Pinning information

Table 2. Pinning

141515 21 1 111111119			
Pin	Description	Simplified outline	Graphic symbol
1, 3, 4, 6, 7, 9, 10, 12	n.c.		44
2	gate1	1 12	11 
5	gate2	- 2         11 3       10	, <b>F</b>
8	drain2	4	13
11	drain1	5       8 6       7	5
13	source [1]		<u>'</u>
		Transparent top view	8 aaa-010780

<sup>[1]</sup> Connected to flange.

# 3. Ordering information

Table 3. Ordering information

Type number	Package	<sup>2</sup> ackage		
	Name	Description	Version	
BLP10H605	HVSON12	plastic thermal enhanced very thin small outline package; no leads; 12 terminals; body $5\times6\times0.85$ mm	SOT1352-1	

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage		-	104	V
$V_{GS}$	gate-source voltage		-6	+11	V
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C

### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	$T_{case} = 80  ^{\circ}C;  P_{L} = 5  W$	[1] <tbd></tbd>	K/W

<sup>[1]</sup>  $R_{th(j-c)}$  is measured under RF conditions

BLP10H605

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Objective data sheet

Rev. 1 — 21 February 2014

NXP Semiconductors

BLP10H605

#### **Broadband LDMOS driver transistor**

### 6. Characteristics

Table 6. DC characteristics

 $T_i = 25$  °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 0.03 \text{ mA}$	104	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 10 \text{ V}; I_{D} = 3 \text{ mA}$	<tbd></tbd>	1.8	<tbd></tbd>	V
$V_{GSq}$	gate-source quiescent voltage	$V_{DS} = 50 \text{ V}; I_D = <\text{tbd}> \text{mA}$	<tbd></tbd>	<tbd></tbd>	<tbd></tbd>	V
I <sub>DSS</sub>	drain leakage current	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}$	-	-	0.6	μΑ
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	<tbd></tbd>	-	Α
$I_{GSS}$	gate leakage current	$V_{GS} = 11 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	60	nA
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = \langle tbd \rangle \text{ mA}$	-	<tbd></tbd>	-	mΩ

#### Table 7. AC characteristics

 $T_i = 25$  °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$C_{rs}$	feedback capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	<tbd></tbd>	-	pF
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 0 \text{ V}; f = 1 \text{ MHz}$	-	<tbd></tbd>	-	pF
C <sub>oss</sub>	output capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	<tbd></tbd>	-	pF

#### Table 8. RF characteristics

Test signal: CW pulsed;  $t_p$  = 50  $\mu$ s;  $\delta$  = 10 %; f = 860 MHz; RF performance at  $V_{DS}$  = 50 V;  $I_{Dq}$  = 30 mA;  $T_{case}$  = 25 °C; unless otherwise specified, in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$G_p$	power gain	$P_L = 5 W$	<tbd></tbd>	<tbd></tbd>	<tbd></tbd>	dB
$\eta_{D}$	drain efficiency	$P_L = 5 W$	<tbd></tbd>	<tbd></tbd>	-	%

### 7. Test information

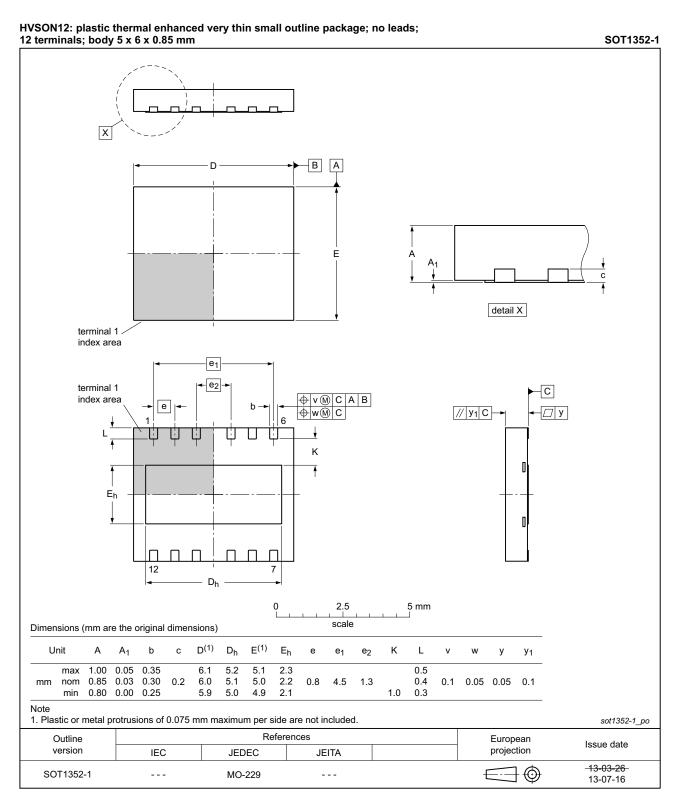
### 7.1 Ruggedness in class-AB operation

The BLP10H605 is capable of withstanding a load mismatch corresponding to VSWR = 35 : 1 through all phases under the following conditions:  $V_{DS}$  = 50 V;  $I_{Dq}$  = 30 mA;  $P_{L}$  = 5 W; f = 860 MHz.

Objective data sheet

4 of 8

#### Package outline 8.



Package outline SOT1352-1 (HVSON12) Fig 1.

Objective data sheet

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# 9. Handling information

### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

### 10. Abbreviations

Table 9. Abbreviations

Acronym	Description
CW	Continuous Wave
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
HF	High Frequency
ISM	Industrial, Scientific and Medical
VSWR	Voltage Standing-Wave Ratio

# 11. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLP10H605 v.1	20140221	Objective data sheet	-	-

Objective data sheet

NXP Semiconductors BLP10H605

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Objective data sheet

Rev. 1 — 21 February 2014

6 of 8

NXP Semiconductors BLP10H605

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# **BLP10H605**

#### **Broadband LDMOS driver transistor**

### 14. Contents

1	Product profile	1
1.1	General description	1
1.2	Features and benefits	1
1.3	Applications	1
2	Pinning information	2
3	Ordering information	2
4	Limiting values	2
5	Thermal characteristics	2
6	Characteristics	3
7	Test information	3
7.1	Ruggedness in class-AB operation	3
8	Package outline	4
9	Handling information	5
10	Abbreviations	5
11	Revision history	5
12	Legal information	6
12.1	Data sheet status	6
12.2	Definitions	6
12.3	Disclaimers	6
12.4	Trademarks	7
13	Contact information	7
14	Contents	٤

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Date of release: 21 February 2014
Document identifier: BLP10H605